## A comparison of bulk-sensitive spectroscopic probes of Yb valence in Kondo systems

L. Moreschini<sup>1</sup>, C. Dallera<sup>2</sup>, J.J. Joyce<sup>3</sup>, J.L. Sarrao<sup>3</sup>, E.D. Bauer<sup>3</sup>, V. Fritsch<sup>3</sup>, S. Bobev<sup>3</sup>, E. Carpene<sup>2</sup>,

G. Monaco<sup>4</sup>, G. Panaccione<sup>5</sup>, P. Lacovig<sup>5</sup>, G. Paolicelli<sup>6</sup>, A. Fondacaro<sup>6</sup>, P. Torelli<sup>7</sup>, and M. Grioni<sup>1</sup>

<sup>1</sup> IPN, Ecole Polytechnique Fédéderale (EPFL), CH-1015 Lausanne, Switzerland

<sup>2</sup> INFM-Dipartimento di Fisica, Politecnico di Milano, p. Leonardo da Vinci 32, 20133 Milano Italy

<sup>3</sup> LosAlamos National Laboratory, Los Alamos, New Mexico 87545, USA

<sup>4</sup> European Synchrotron Radiation Facility (ESRF), 38043 Grenoble Cédex, France

<sup>5</sup> Laboratorio TASC, INFM, Area Science Park, S.S. 14, Km 163.5

<sup>6</sup> INFM and Dipartimento di Fisica, Universitá di Roma III, I-00146 Roma, Italy

<sup>7</sup> LURE, Université de Paris-Sud, F-91898 Orsay, France

## (Dated: August 12, 2006)

We exploited complementary synchrotron radiation spectroscopies to study the Yb 4f electronic configuration in three representative intermediate-valence materials: YbAl<sub>3</sub>, YbInCu<sub>4</sub>, and YbCu<sub>2</sub>Si<sub>2</sub>. High-resolution x-ray absorption (PFY-XAS), resonant inelastic x-ray scattering (RIXS) and hard x-ray photoemission (HAXPES) data all show characteristic temperature-dependent changes of the Yb valence. For each material, the increments measured from low (20 K) to high (300 K) temperature by the different probes are quite similar. The estimated RIXS and XAS valences are consistently higher than the HAXPES values. We briefly discuss the possible origin of this discrepancy.

PACS numbers: 71.28.+d, 78.70.En, 78.70.Dm, 79.60.-i

High-energy spectroscopies like photoemission (PES) or xray absorption (XAS) provide unique insight in the dynamics of the 4f electrons that are at the origin of 'Kondo' phenomena in intermediate valence (IV) materials, like many Ce or Yb metallic compounds<sup>1–3</sup>. The fractional occupancy  $n_f$  of these states reflects their hybridization with extended conduction band electrons. The Anderson Impurity Model (AIM), that embodies the minimal theoretical description of this phenomenon, predicts for  $n_f$  a simple dependence on hybridization and temperature<sup>4</sup>, via the single parameter ( $T/T_K$ ).  $T_K$  is the material-dependent Kondo temperature. It grows exponentially with the 4f-band hybridization, and sets the lowenergy scale of the problem. It is generally assumed that these generic features of the AIM survive in the more elaborate and applicable theoretical lattice schemes<sup>5</sup>.

Some aspects of a scaling behavior have been confirmed qualitatively by conventional XAS<sup>6-8</sup> and core level PES<sup>9</sup> in Ce and Yb IV compounds, and even quantitatively by more elaborate photon in - photon out experiments<sup>10</sup>. Scaling should be especially evident in valence band PES data, since the intensity of the Kondo resonance (KR), the characteristic many-body feature straddling the Fermi level<sup>4,11</sup>, directly reflects the configuration mixing in the ground state. PES data, on the contrary, have been controversial, with results from cleaved single crystals<sup>12,13</sup> failing to exhibit the  $T/T_K$  dependence generally observed in polycrystalline samples<sup>2,3,14,15</sup>. The issue is confused by the short probing depth (5-10  $\text{\AA}$ ) of low-energy PES, and by the tendency of the Yb (Ce) ions to adopt a surface electronic configuration different from that of the bulk. More recent soft<sup>16-20</sup> and hard x-ray PES (HAXPES)<sup>19,21</sup> experiments with enhanced bulk sensitivity generally support a Kondo scenario interpretation.

The purpose of the present paper is to compare intrinsically bulk-sensitive photon in - photon out spectroscopies like XAS and resonant inelastic x-ray spectroscopy (RIXS) with HAXPES. We present data on three representative Yb IV compounds: YbAl<sub>3</sub>, YbInCu<sub>4</sub>, and YbCu<sub>2</sub>Si<sub>2</sub>. YbCu<sub>2</sub>Si<sub>2</sub> and YbAl<sub>3</sub> are typical Kondo systems, with Kondo temperatures  $T_K \sim 40$ -60 K and, respectively,  $T_K \sim 400$ K<sup>12,14</sup>. YbInCu<sub>4</sub> exhibits at T<sub>V</sub>=42 K an isostructural firstorder transition that affects the electronic and magnetic properties. The valence suddenly increases from 2.83 to 2.96 for T>T<sub>V</sub>, while the Kondo temperature drops from  $T_K \sim 400$  K (T<T<sub>V</sub>) to  $T_K \sim 20$  K (T>T<sub>V</sub>)<sup>22,23</sup>.

We show that the different spectroscopies agree on two major points. Firstly, they all indicate an increase of the Yb valence (at 20 K) from YbAl<sub>3</sub> to YbCu<sub>2</sub>Si<sub>2</sub>, in agreement with the known properties of the three compounds. Secondly, they reveal the expected increase of the Yb valence with temperature. The valence values extracted from the XAS/RIXS data are closer to the estimates from non spectroscopic measurements. Photoemission provides a more direct view of the Yb 4*f* states, but it remains, even at high energy, more sensitive to the sample preparation procedure. In our experiment, the perturbation produced by scraping the surface may well have extended over a thickness comparable to - and possibly larger than - the probing depth of HAXPES (~ 60Å). We conclude that XAS/RIXS is the more consistent probe of the bulk Yb electronic configuration.

We have used flux-grown single crystals characterized by x-ray diffraction and magnetic susceptibility measurements. All measurements were performed at the undulator beamline ID16 of the ESRF (Grenoble) equipped with a Si(111) double crystal monochromator. For partial fluorescence yield XAS (PFY-XAS) and RIXS experiments, freshly scraped samples were mounted on a He cryostat and measured in high  $(10^{-8} \text{ mbar})$  vacuum. We used a Rowland circle spectrometer based on a spherically bent Si(620) crystal, and a Si avalanche pho-



FIG. 1: a) PFY-XAS spectra of three IV compounds and of divalent Yb<sub>14</sub>MnSb<sub>11</sub> at 20 K and 300 K. b) RIXS spectra measured bewteen 20 K and 300 K, at  $h\nu_{in}$ =8.941 keV, the maximum of the Yb<sup>2+</sup> resonance profile.

todiode detector. The total energy resolution was ~1.5 eV. For HAXPES the beamline was equipped with a Si(333) channelcut post-monochromator working in near backscattering condition at hv=5934 eV. The samples were scraped by a diamond file at  $10^{-9}$  mbar, and measured by the VOLPE electron spectrometer<sup>24</sup>. The combined (photons + electrons) energy resolution now attainable by this instrument is  $\Delta E \sim 70$ meV, but for the present experiment we used a lower resolution  $\Delta E \sim 0.25$  eV in a trade-off for intensity.

The PFY-XAS and RIXS results for the IV materials and for the divalent reference compound Yb<sub>14</sub>MnSb<sub>11</sub> are summarized in Fig. 1. The Yb L<sub>3</sub> PFY-XAS spectra measure, as a function of the incident photon energy, the intensity of the L $\alpha_1$  ( $3d \rightarrow 2p$ ) fluorescence (h $\nu_0$ =7415 eV) emitted after the creation of an Yb 2p hole:  $2p^64f^N \rightarrow 2p^54f^N\varepsilon d \rightarrow$  $2p^63d^94f^N$ . The intrinsic spectral line width is set by the shallower 3d hole ( $\Delta E \sim 0.6$  eV), rather than by the deep 2p hole ( $\Delta E \sim 5.3$  eV) as in conventional XAS. PFY-XAS is not strictly equivalent to XAS with a reduced line width, but it gives acces to finer spectral details<sup>25–27</sup>. The Yb L $\alpha$  RIXS spectra reproduce, for a given h $\nu_{in}$ , the energy distribution of the photons emitted in the same de-excitation channel. The energy transfer ( $h\nu_{in} - h\nu_{out}$ ) is the energy difference between the excited final state and the ground state.

In Yb IV materials,  $L_3$  (PFY-)XAS is a superposition of absorption spectra from the Yb<sup>2+</sup> and Yb<sup>3+</sup> components of the hybrid ground state. The intensities of each contribution for our analysis is assumed proportional to the weight of the corresponding initial state configurations<sup>8</sup>. The spectra of Fig.

The RIXS spectra similarly exhibit  $Yb^{2+}$  and  $Yb^{3+}$  components, which can be selectively enhanced by an appropriate choice of the incident photon energy. The spectra of Fig. 1b correspond to the maximum of the Yb<sup>2+</sup>XAS (and RIXS) signal. This is a favorable condition because small valence changes have a larger effect on the minority Yb<sup>2+</sup> weight. Changes in the Yb<sup>2+</sup> intensity reflect corresponding *relative* changes of the Yb<sup>2+</sup>weight in the initial state. Knowledge of the Yb valence at e.g. 300 K, either from the XAS spectrum, or by a combined analysis of the  $Yb^{2+}$  and  $Yb^{3+}$  resonance profiles<sup>27</sup>, yields the valence v(T) at all temperatures. For YbAl3 and YbInCu4 we also performed continuous measurements of the Yb<sup>2+</sup> RIXS intensity at a rate of  $\sim$ 1 K/minute. v(T) (Fig. 4) follows a smooth 'Kondo' dependence in YbAl<sub>3</sub>, and the overall valence increase is  $\Delta v=0.05$ . In YbInCu<sub>4</sub> the Yb valence exhibits a jump at  $T_V$ =42 K, and no further evolution above  $T_V$ , as expected from  $T_K \sim 20$  K in the high-temperature phase. v(T) does not saturate to the low-T value immediately below  $T_V$ , in contrast to the electrical resistivity or the magnetic susceptibility<sup>23</sup>. The further low-T evolution suggests a distribution of  $T_V$ 's, possibly associated with disorder induced by scraping, and extending over a distance comparable with the probing depth of RIXS ( $\gg100$ Å). This is much larger than the thickness of a proposed perturbed region under a cleaved surface, as estimated by  $PES^{20}$ . Nonetheless, the RIXS data of Fig. 4 is clear spectroscopic evidence of a first-order-like transition at  $T_V$ .

The valence band (VB) and Yb 3d core level HAXPES results are shown in Fig. 2 and Fig. 3, after the usual subtraction of inelastic Shirley backgrounds. The VB spectra exhibit the typical features of IV Yb compounds: the spin-orbit-split Yb<sup>2+</sup> KR near  $E_F$ , and an Yb<sup>3+</sup> multiplet at 5-12 eV. Peaks at  $\sim 4 \text{ eV}$  in YbInCu<sub>4</sub> and YbCu<sub>2</sub>Si<sub>2</sub> are from Cu 3d states. At this photon energy (h $\nu$ =5935 eV) the contribution from the topmost surface layer is small  $(\sim 5\%)^{28}$ , and the spectra are free from the broad surface signal typical of low-energy PES. The Yb<sup>3+</sup>intensity in YbInCu<sub>4</sub> is somewhat smaller than in published HAXPES data<sup>21</sup>. The (Yb<sup>2+</sup>/Yb<sup>3+</sup>) intensity ratio at 300 K is largest for YbAl<sub>3</sub> and smallest for YbInCu<sub>4</sub>, and in all compounds the intensity of the divalent doublet decreases at high temperature, with a corresponding growth of the Yb<sup>3+</sup>multiplet. Notice that the simple thermal broadening of the Fermi edge would not affect the integrated intensity of a band feature. The VB HAXPES results are therefore consistent with the RIXS data of Fig. 1, and with a Kondo scenario.

The Yb valence can be estimated from the Yb<sup>2+</sup>and Yb<sup>3+</sup>VB PES intensities as: v=2+  $14 \cdot I(3+)/[14 \cdot I(3+)+13 \cdot I(2+)].$ We have isolated the 4fsignal in YbInCu<sub>4</sub> by comparison with the spectrum of LuInCu<sub>4</sub>, shown in Fig. 2 after removing the atomic-like Lu 4f doublet centered at  $\sim 8$  eV. Integrating the difference spectrum over 2+ and 3+ energy windows, yields v(20 K)= $(2.65\pm0.03)$  and v(300 K)= $(2.77\pm0.03)$ . For YbAl<sub>3</sub> and



FIG. 2: HAXPES ( $h\nu$ =5935 eV) valence band spectra measured at 20 K (thin solid lines) and 300 K (thick (red) solid lines). The dashed line is the spectrum of LuInCu<sub>4</sub>, after subtraction of the atomic-like 4*f* doublet. The dotted lines are phenomenological non-4*f* backgrounds (see text).

YbCu<sub>2</sub>Si<sub>2</sub> the corresponding Lu compounds could not be measured, and we used information from published soft x-ray VB spectra<sup>12</sup>. Assuming, as a first approximation, the same photon energy dependences for the 4f/(non-4f) intensity ratio as in YbInCu<sub>4</sub>, yields the values reported in Fig. 4. In both cases the correction from the non-4f states is small ( $\Delta v \sim 0.06$ ). Subtracting phenomenological backgrounds from the spectra (dotted lines), yields similar results. The error bars are large but acceptable, since our goal is to compare the different probes, rather than to determine the Yb valence with high accuracy.

The 3d core levels are good indicators of the electronic configuration in 4f materials. The Yb 3d lines are too deep for standard Al K $\alpha$  sources, but can be reached by HAXPES. The j=3/2 and j=5/2 spin-orbit-split manifolds, separated by ~50 eV, are further split into a sharp  $3d^94f^{14}$  (Yb<sup>2+</sup>) final state and a  $3d^94f^{13}$  (Yb<sup>3+</sup>) multiplet (Fig. 3). Broad plasmon features are observed ~25 eV below the leading peak<sup>21</sup>. YbAl<sub>3</sub> also exhibits, besides plasmon replicas, a very intense Al 1s peak, with an associated strong satellite. We have determined the Yb valence by integrating the intensity of the j=5/2 manifolds within separate 2+ and 3+ energy windows. The contribution of the overlapping plasmon satellite in YbAl<sub>3</sub> was removed by subtracting a scaled replica of the



FIG. 3: Low-temperature spectra of the Yb 3d core levels.Each spinorbit manifold is split into 2+ and 3+ components. The arrows mark strong plasmon satellites in YbAl<sub>3</sub>. The asterisk marks a plasmon replica of the strong Al 1s peak.

3+ line shape, from the YbCu<sub>2</sub>Si<sub>2</sub> spectrum.

The experimental results are summarized in Fig. 4. The RIXS valence is always largest, and consistent with previous XAS data (Table I). The agreement with thermodynamic and magnetic measurements is rather good. As already noted, the RIXS temperature dependence displays, as expected, a smooth variation in YbAl<sub>3</sub> and a step at  $T_V$  in YbInCu<sub>4</sub>. As to photoemission, there is a considerable scattering in the literature (Table I), with low-energy PES results showing lower valences than soft- and hard x-ray PES. Our core level results are consistent with the latter, and smaller by 0.05 to 0.1 than the RIXS values. The data points are too sparse to confirm the sharp jump in YbInCu<sub>4</sub>, suggested by Ref. 21. At present, the low signal forbids a continuous T-dependent HAXPES measurement.

The VB spectra yield consistently lower values than the 3d core data. In YbAl<sub>3</sub> it may point to an inadequate background removal procedure. This problem is especially delicate in HAXPES. For instance, the Yb(4f)/Al(3s) atomic cross sections ratio decreases by one order of magnitude between 1000 eV and 6000 eV<sup>29</sup>. A comparison with Lu or La sister compounds would therefore be desirable. The difference is smaller for YbCu<sub>2</sub>Si<sub>2</sub> and YbInCu<sub>4</sub>. In the latter the valence transition is smeared over 50 K, which again suggests the possible shortcomings of scraping the surface for HAX-PES. Remarkably, the measured relative valence changes are quite similar for all techniques. This suggests further systematic studies of the origin of the discrepancies, namely varying the photon energy (probing depth) and comparing data from

	YbAl <sub>3</sub>	YbInCu <sub>4</sub>	YbCu <sub>2</sub> Si <sub>2</sub>
PES (h $\nu \leq 120 \text{ eV}$ )	2.63 <sup>12</sup>	2.57(20 K) - 2.86 (300 K) <sup>20</sup>	2.63 <sup>12</sup>
PES (h $\nu \ge 500 \text{ eV}$ )	2.77 (10 K) <sup>14</sup> ; 2.65 (20 K) <sup>19</sup>	2.67(20 K) - 2.83 (300 K) <sup>18,20</sup> 2.60(20 K) - 2.72 (70 K) <sup>30</sup>	
Core level HAXPES	2.71 (180 K) <sup>19</sup>	2.74(10 K) - 2.90 (220 K) <sup>21</sup>	
XAS	2.78 (20 K) - 2.83 (300 K) <sup>8</sup>	2.83(20 K) - 2.96 (300 K) <sup>31</sup>	2.82(20 K) - 2.89 (300 K) <sup>8</sup>



FIG. 4: Summary of the valence values determined by the various spectroscopies. The solid lines refer to continuous temperature-dependent RIXS measurements.

scraped and cleaved samples. From the thoretical side, first principles calculations of the PES and XAS spectra, including dynamical effects<sup>32</sup>, would reduce the uncertainties of the present analysis, and could reveal possible systematic differences between the two spectroscopic probes.

In summary, we have presented a comparison of photon in - photon out and high-energy PES results in three representative IV materials. The data generally display a temperature and  $T_K$  dependence consistent with a Kondo scenario, and quite similar values for the relative valence changes. They also show quantitative differences. RIXS and high-resolution PFY-XAS show  $n_f$  values more consistent with thermodynamic models. HAXPES, albeit not totally free from the influence of surface disorder and surface preparation techniques, is much more bulk sensitive than standard PES, and provides a unique and direct view of the 4f many-body spectral features.

We gratefully acknowledge the expert support of the ESRF staff. The HAXPES electron spectrometer has been developed by the VOLPE collaboration<sup>24</sup> and supported by the EU under Contract HPRI-CT-2001-50032 and by the Swiss National Science Foundation. LANL support was provided by the US-DOE under OBES.

- <sup>1</sup> A.C. Hewson, *The Kondo Problem to Heavy Fermions*, (Cambridge University Press, 1993).
- <sup>2</sup> Allen *et al.*, Adv. Phys.**35**,275 (1986).
- <sup>3</sup> D. Malterre, M. Grioni, and Y. Baer, Adv. Phys. 45, 299 (1996).
- <sup>4</sup> N.E. Bickers, D.L. Cox, and J.W. Wilkins, Phys. Rev. B **36**, 2036 (1987).
- <sup>5</sup> A.N. Tahvildar-Zadeh, M. Jarrel, and J.K. Freericks, Phys. Rev. Lett. **80**, 5168 (1998).
- <sup>6</sup> J. Röhler, J. Magn. Magn. Mat. **47-48**, 175 (1985)
- <sup>7</sup> E. Beaurepaire, J.P. Kappler, and G. Krill, Solid State Commun. **57**, 145 (1986).
- <sup>8</sup> J.M. Lawrence, G.H. Kwei, P.C. Canfield, J.G. DeWitt, and A.C. Lawson, Phys. Rev. B **49**, 1627 (1994).
- <sup>9</sup> J.C. Fuggle *et al.*, Phys. Rev. B **27**, 7330 (1983).
- <sup>10</sup> C. Dallera *et al.*, Phys. Rev. Lett. **88**, 196403 (2002).

- <sup>11</sup> O. Gunnarsson and K. Schönhammer, Phys. Rev. 28, 4315 (1983).
- <sup>12</sup> J.J. Joyce *et al.*, Phys. Rev. **54**, 17515 (1996).
- <sup>13</sup> J.J. Joyce, A.J. Arko, L.A. Morales, J.L. Sarrao, and H. Höchst, Phys. Rev. **63**, 197101 (2001).
- <sup>14</sup> L.-H. Tjeng *et al.*, Phys. Rev. Lett. **71**, 1419 (1993).
- <sup>15</sup> P. Weibel *et al.*, Z. Phys. B **91**, 337 (1193).
- <sup>16</sup> E. Weschke et al., Phys. Rev. B **44**, 8304 (1991).
- <sup>17</sup> A. Sekiyama *et al.*, Nature (London) **403**, 396 (2000).
- <sup>18</sup> H. Sato *et al.*, Phys. Rev. B **69**, 165110 (2004).
- <sup>19</sup> S. Suga et al., J. Phys. Soc. Jpn 74, 2880 (2005).
- <sup>20</sup> S. Schmidt, S. Hüfner, F. Reinert, and W. Assmus, Phys. Rev. B 71, 195110 (2005).
- <sup>21</sup> H. Sato et al., Phys. Rev. Lett. 93, 246404 (2004).
- <sup>22</sup> Felner and I. Nowik, Phys. Rev. B **33**, 617 (1986).
- <sup>23</sup> J.L. Sarrao *et al.*, Phys. Rev. B **54**, 12207 (1996).

- <sup>24</sup> P. Torelli *et al.*, Rev. Sci. Instrum. **76**, 023909 (2005).
- <sup>25</sup> K. Hämäläinen, D.P. Siddons, J.B. Hastings, and L.E. Berman, <sup>26</sup> A. Kotani and S. Shin, Rev. Mod. Phys. **73**, 203 (2001).
   <sup>27</sup> C. Dallera *et al.*, Phys. Rev. B **68**, 245114 (2003).
   <sup>28</sup> M. Sacchi *et al.*, Phys. Rev. B **71**, 155117 (2005).

- <sup>29</sup> J.J. Yeh and I. Lindau, At. Data Nucl. Data Tables **32**, 1 (1985).
  <sup>30</sup> D.P. Moore *et al.*, Phys. Rev. B **62**, 16492 (2000).
  <sup>31</sup> A.L. Cornelius *et al.*, Phys. Rev. B **56**, 7993 (1997).

- <sup>32</sup> O. Wessely, M.I. Katsnelson, and O. Eriksson, Phys. Rev. Lett. 94, 167401 (2005).